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Multivariate numerical optimization of an InGaN-based hetero junction solar cell



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Summary

Because of remarkable properties of InGaN, we simulated and optimized an InGaN-based dual-junction solar cell connected by a specifically designed tunnel junction. The device is simulated in the framework of a drift-diffusion model using the ATLAS device simulation framework from the Silvaco company. The optimization is done by coupling ATLAS with multivariate mathematical optimization methods based on state-of-the-art optimization algorithms. For that, we used a Python package that we developed in the SAGE software interface. The objective is to optimize the conversion efficiency of the solar cell by simultaneously optimizing several physical and geometrical parameters of the solar cell. It is an unprecedented multivariate optimization for solar cells which takes into account the correlation between these parameters. For this solar cell, we optimized simultaneously 11 parameters of the structure. An optimum conversion efficiency of 24% was predicted for this designed solar cell.

Multivariate Optimization

Standard-Method: Parametric Analysis

- One parameter is varying while the other parameters are kept **constant**
- Have not taken into account, the complexity of the interdependence of parameters
- Application difficult to design components

Our Method: Mulvariate Optimization

- Simultaneously optimizing of several physical and geometrical parameters
- Much more rigorous than single parametric analysis
- Suitable for next generation solar cell
- **Optimum efficiency** as a function of several optimization parameters

Mathematical Optimization

- Three algorithms (state-of-the-art)
- 1-TNC (Truncated Newton Algorithm)
- 2-SLSQP (Sequential Least SQuares Programming)
- 3- L-BFGS-B (Quasi-Newton Method)

□ Sage/Scipy

- We use the Sage software interface to the Scipy optimizers
- Open source free sofware

Numerical Simulation

Multivariate Optimization

Gimulation: Drift-Diffusion Model

Current equations

 $J_n = qn\mu_n E + qD_n \frac{dn}{dx}$ $J_p = qp\mu_p E + qD_p \frac{dp}{dx}$

En

• Poisson's equation $\nabla E = \frac{\rho}{2}$

q : electronic charge,	n : electron density,
p : electron density,	μ : carrier mobility,
<i>E</i> : Electric field,	D : Diffusion coefficient.
ho : Charge density	$\boldsymbol{\varepsilon_0}$: Permitivity

Using ATLAS (Silvaco company software)

Physical modeling using Experimental data to tune well known models:

- <u>Carrier Mobility :</u>
 Caughey-Thomas model
- <u>Carrier Recombination :</u>
 Shockley-Read-Hall (SRH) , direct and Auger recombination models
- Index of refraction : Adachi model
- <u>Absorption coefficient :</u>
 Phenomenological Model

Coded and optimized by computer experts

Multijunction InGaN Solar Cell

Solar Cell Structure

InGaN-based double-junction solar cell

- Structure composed of two p-n junctions
- Two subcell vertically stacked having different bandgaps

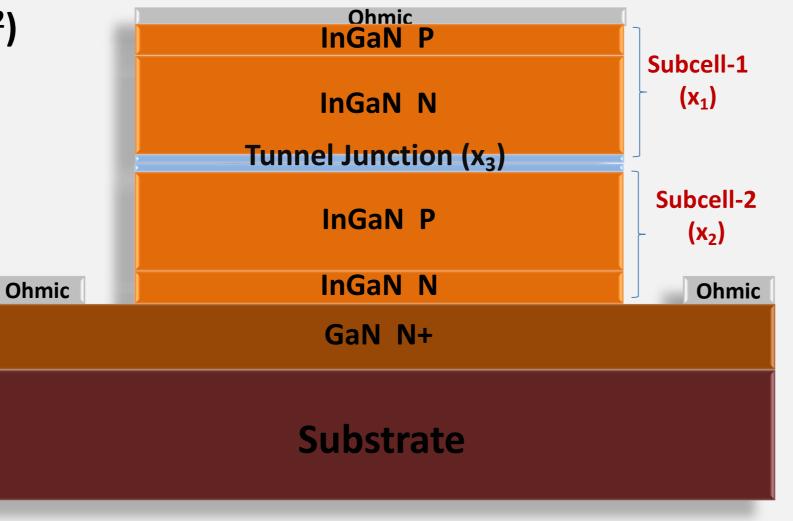
Structure under AM1.5 illumination (100mW=cm²)

- Subcell-1, absorbs high-energy photons
- Subcell-2, absorbs lower energies photons
- The Solar cell absorbs a larger solar spectrum than a single junction cell

Tunnel junction

- The two subcells are connected by a tunnel junction to enhance current matching between the subcells
- X₁, X₂ and x₃ Indium composition of subcell-1, subcell-2 and tunnel junction respectively





Optimal Results

11 Parameters of solar cell are optimized simultaneously

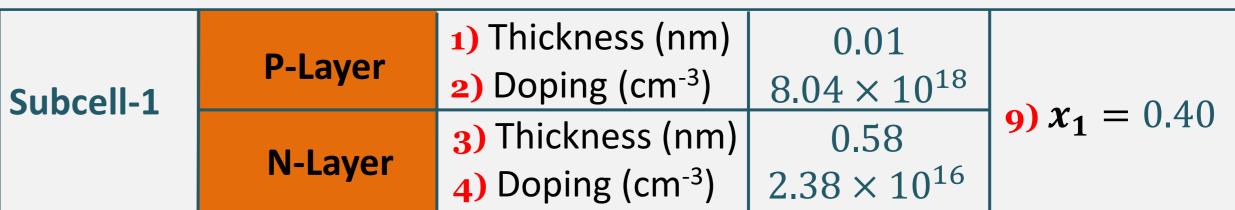
- Obviously the optimization problem becomes more complex with so many variables
- Optimization method with a higher-order convergence
- Ensure the overall convergence of the optimization method

<u>11</u> Optimization parameters concerns the **dopings** and the **thicknesses** of the **2 subcells** and the different **indium compositions** (x_1, x_2, x_3) .

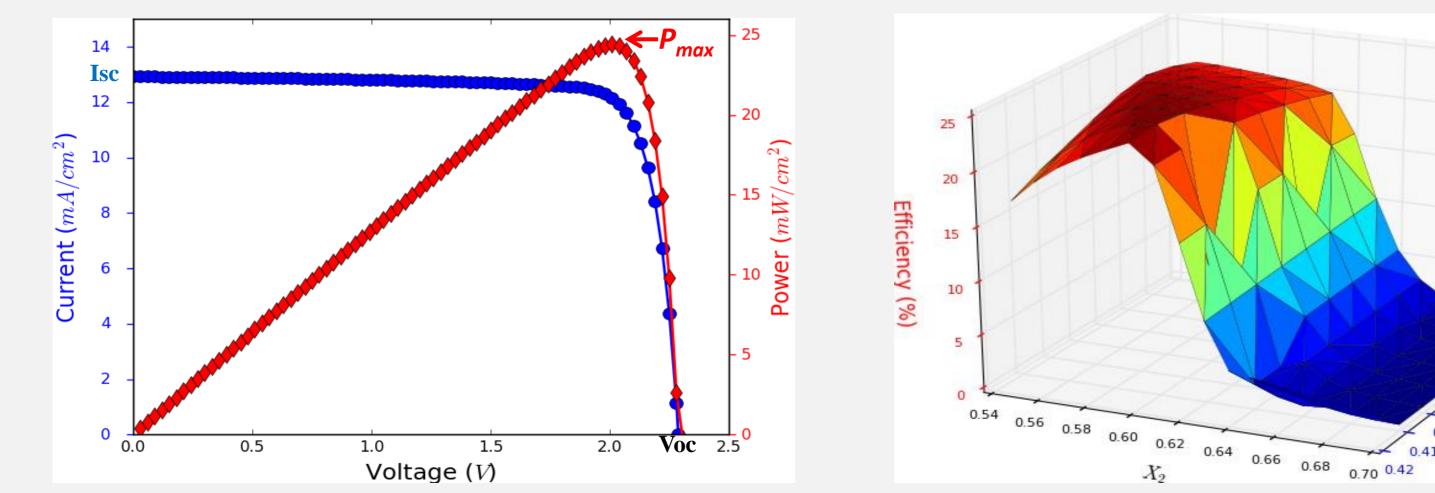
□ Their **optimization intervals** are as follows:

- The Indium composition is x in $In_xGa_{(1-x)}N$: [0.00 1.00]
- The InGaN layer n-type and p-type doping : $[1.10^{16} 1.10^{19}]cm^{-3}$
- The InGaN layer thickness :
- $[1.10^{16} 1.10^{19}]cm^{-3}$ $[0.01 - 1.00]\mu m$

□ Their **optimal values** are in the following table:



Solar Cell Performances



Current-voltage and power-voltage characteristic curves. P_{max} the maximum power of solar cell

Efficiency as a function of the Indium compositions, X1 for the top cell and X2 for the bottom cell

Tunnel Junction				10) $x_3 = 0.50$
Subcell-2P-LayerN-Layer	P-Layer	 5) Thickness (nm) 6) Doping (cm⁻³) 	0.57 2.51×10^{18}	
	 7) Thickness (nm) 8) Doping (cm⁻³) 	0.01 1.00×10^{17}	11) $x_2 = 0.59$	

Optimal efficiency and the significant parameters of the solar cell

 $\begin{array}{l} \text{The short-circuit current, } J_{SC} = 12.92mA/cm^2\\ \text{The open-circuit voltage, } V_{OC} = 2.287\,V\\ \text{Fill factor,} & FF = 82.55 \end{array}$